

## **Description**

The DMTH4008LPSQ-13 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## **General Features**

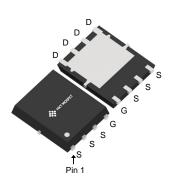
 $V_{DS} = 40V I_D = 55A$  $R_{DS(ON)} < 8.5m\Omega V_{GS}=10V$ 

# **Application**

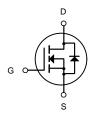
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
DMTH4008LPSQ-13	DFN5X6-8L	HXY MOSFET	5000

#### Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units		
V <sub>D</sub> s	Drain-Source Voltage	40	V		
Vgs	Gate-Source Voltage	Gate-Source Voltage ±20			
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	55	Α		
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	41	Α		
Ірм	Pulsed Drain Current <sup>2</sup>	280	Α		
EAS	Single Pulse Avalanche Energy <sup>3</sup>	76	mJ		
Тѕтс	Storage Temperature Range	-55 to 175	°C		
TJ	Operating Junction Temperature Range	-55 to 175	°C		



# Electrical Characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	40			V
D	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =15A		6.5	8.5	mΩ
R <sub>DS(ON)</sub>		V <sub>GS</sub> =4.5V , I <sub>D</sub> =8A		9	12	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.8	2.5	V
l	Drain-Source Leakage Current	V <sub>DS</sub> =40V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
I <sub>DSS</sub>		V <sub>DS</sub> =40V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS=\pm 20V}$ , $V_{DS}$ =0V			±100	nA
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		2.0		Ω
Qg	Total Gate Charge (4.5V)			19.7		
Qgs	Gate-Source Charge	-Source Charge V <sub>DS</sub> =20V , V <sub>GS</sub> =10V , I <sub>D</sub> =10A		2.8		nC
Q <sub>gd</sub>	Gate-Drain Charge			5.1		
T <sub>d(on)</sub>	Turn-On Delay Time			13.2		
Tr	Rise Time	$V_{DD}$ =15V , $V_{GS}$ =10V , $R_{G}$ =3.3 $\Omega$		2.2		
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =1A		72		ns
T <sub>f</sub>	Fall Time			4.5		
Ciss	Input Capacitance			6000		
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		1509		pF
Crss	Reverse Transfer Capacitance			129		
Is	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			140	Α
$V_{\text{SD}}$	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1	V

#### Note:

- 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 3. The EAS data shows Max. rating . The test condition is  $V_{DD}$ =25V, $V_{GS}$ =10V,L=0.1mH, $I_{AS}$ =31A
- 4.The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



## **Typical Characteristics**

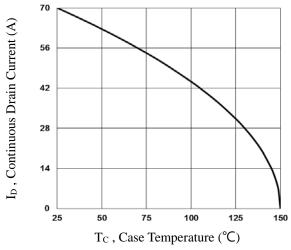


Fig.1 Continuous Drain Current vs. T<sub>C</sub>

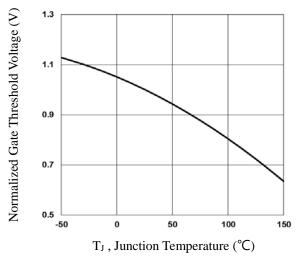


Fig. 3 Normalized V<sub>th</sub> vs. T<sub>J</sub>

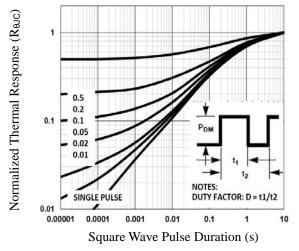


Fig.5 Normalized Transient Impedance

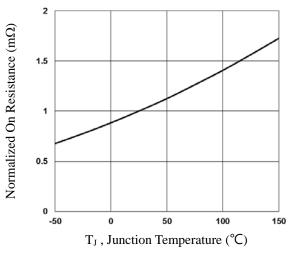


Fig. 2 Normalized RDSON vs. TJ

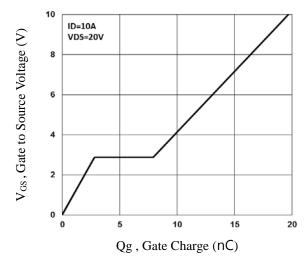


Fig.4 Gate Charge Waveform

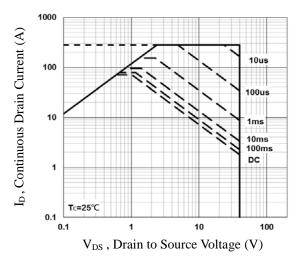


Fig.6 Maximum Safe Operation Area

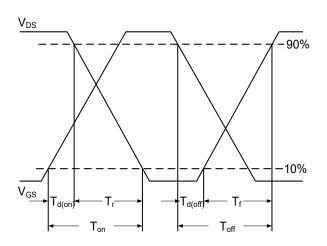


Fig.7 Switching Time Waveform

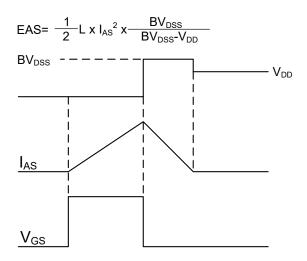
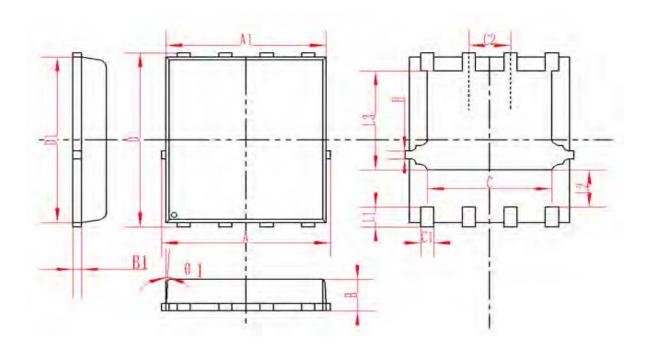


Fig.8 EAS Waveform



# **DFN5X6-8L Package Information**



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010

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